Hyeon-Bhin Jo

List of Publications by Year
in descending order

11	108	1936888 4	1588620 8
papers	citations	h-index	g-index

11	11	11	90
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Physics-Based Analytical Channel Charge Model of In _x Ga_{1-x}As/In_{0.5}2Al_{0.48}As Quantum-Well Field-Effect Transistors From Subthreshold to Strong Inversion Regimes. IEEE Journal of the Electron Devices Society, 2022, 10, 387-396.	1.2	1
2	Impact of Sulfur Passivation on Carrier Transport Properties of In_{0.7}Ga_{0.3}As Quantum-Well MOSFETs. IEEE Journal of the Electron Devices Society, 2021, 9, 209-214.	1.2	3
3	Theoretical and experimental analysis of the source resistance components in In0.7Ga0.3As quantum-well high-electron-mobility transistors. Journal of the Korean Physical Society, 2021, 78, 516-522.	0.3	3
4	Sub-30-nm In_{0.8}Ga_{0.2}As Composite-Channel High-Electron-Mobility Transistors With Record High-Frequency Characteristics. IEEE Transactions on Electron Devices, 2021, 68, 2010-2016.	1.6	13
5	A Comprehensive Benchmarking Method for the Net Combination of Mobility Enhancement and Density-of-States Bottleneck. IEEE Electron Device Letters, 2021, 42, 804-807.	2.2	0
6	$ext{In}_{x}ext{Ga}_{1-x}ext{As}$ quantum-well high-electron-mobility transistors with a record combination of $mathrm{f}_{mathrm{T}}$ and $mathrm{f}_{max}$: From the mobility relevant to ballistic transport regimes. , 2021, , .		0
7	L_g = 19 nm In_{0.8}Ga_{0.2}As composite-channel HEMTs with f_T = 738 GHz and f_{max} = 492 GHz. , 2020, , .		9
8	L_gÂ=Â25Ânm InGaAs/InAlAs high-electron mobility transistors with both f_T and f_{max} in excess of 700 GHz. Applied Physics Express, 2019, 12, 054006.	1.1	30
9	Long-channel InAlAs/InGaAs/InAlAs single-quantum-well MISFETs with subthreshold swing of 61ÂmV/decade and effective mobility of 11 900Âcm²ÂV^{â^'1}ÂÂ·Âs^{â^'1}. Applied Physics Express, 2019, 12, 064003.	2.3	3
10	Impact of the Source-to-Drain Spacing on the DC and RF Characteristics of InGaAs/InAlAs High-Electron Mobility Transistors. IEEE Electron Device Letters, 2018, 39, 1844-1847.	2.2	17
11	<inline-formula> <tex-math notation="LaTeX">${L}_{{g}} = {87}$ </tex-math> </inline-formula>nm InAlAs/InGaAs High-Electron- Mobility Transistors With a <italic>g</italic> _{m_max} of 3 S/mm and <inline-formula> <tex-math notation="LaTeX">$f_{{T}}$ </tex-math> </inline-formula> of 559 GHz. IEEE Electron Device Letters, 2018, 39, 1640-1643.	2.2	29